Not Recommended for New Design - Use PI2MEQX2503A

A Product Line of Diodes Incorporated

PI2MEQX2503

2.5Gbps, MIPI CSI-2/DSI D-PHY ReDriver

Description

The PI2MEQX2503 is a low power, high performance 2.5Gbps two lanes data and clock MIPI D-PHY ReDriver™. The device complies with MIPI D-PHY1.2 standard and can be used in either a MIPI CSI-2 or MIPI DSI application at datarates of up to 2.5Gbps in D-PHY.

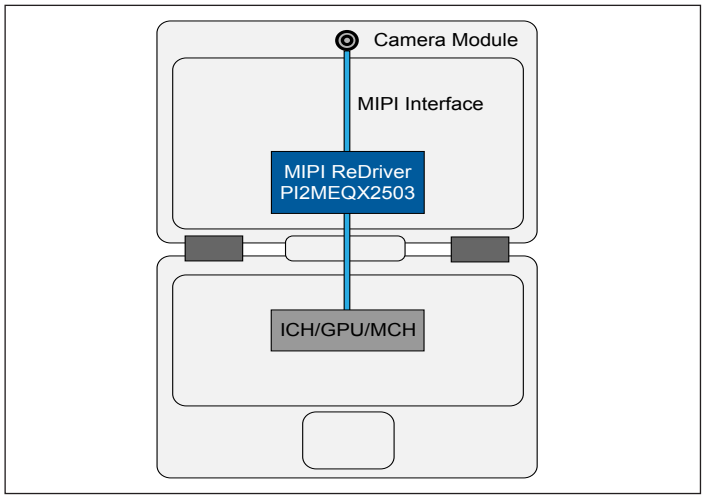
The device compensates for PCB, connector, and cable related loss and switching related loss to provide the optimum electrical performance from a CSI2/DSI source to sink. The inputs of PI2MEQX2503's feature configurable equalizers.

The PI2MEQX2503 output voltage swing and edge rate can be adjusted by changing the pin state. It is optimized for mobile applications, and contains activity detection circuitry on the D-PHY Link interface that can transit into a lower power mode when in ULPS and LP states.

Application(s)

- Laptops, All-in-one PCs
- Drones, Robots
- TVs, Commercial Displays
- Smart Home Devices
- AR Glasses
- Embedded Systems

Typical MIPI Re-Driver in NB Application



Features

- MIPI D-PHY1.2 Specification Compliant
- Enables Low-Cost Cable Solutions
- Supports 2-Lanes at 2.5Gbps in D-PHY
- Sub mW Power in Shutdown State
- Supports MIPI DSI Bi-Directional LP Mode
- Supports ULPS and LP Power States
- Supports I2C Slave Mode Setting
- Pin Strap Value Sampled on Rising Edge of RSTN
- Adjustable Output Voltage Swing
- Selectable TX Pre-Emphasis Levels
- Adjustable Rx EQ to Compensate Insertion Loss
- Configurable Edge Rate Control
- Dynamic Data Compensation
- Industrial Temperature Range: –40°C to 85°C
- Available in Single 1.8V - Supply
- Packaging (Pb-free & Green):
  - 24-pin, 2mm x 4mm, X1QFN (XEA)
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- For automotive applications requiring specific change control (i.e. parts qualified to AEC-Q100/101/104/200, PPAP capable, and manufactured in IATF 16949 certified facilities), please contact us or your local Diodes representative. https://www.diodes.com/quality/product-definitions/

Ordering Information

Orderable Part Number	Package Code	Package Description
PI2MEQX2503XEAEX	XEA	24-contact, Extra Thin Fine Pitch QFN (X1QFN)

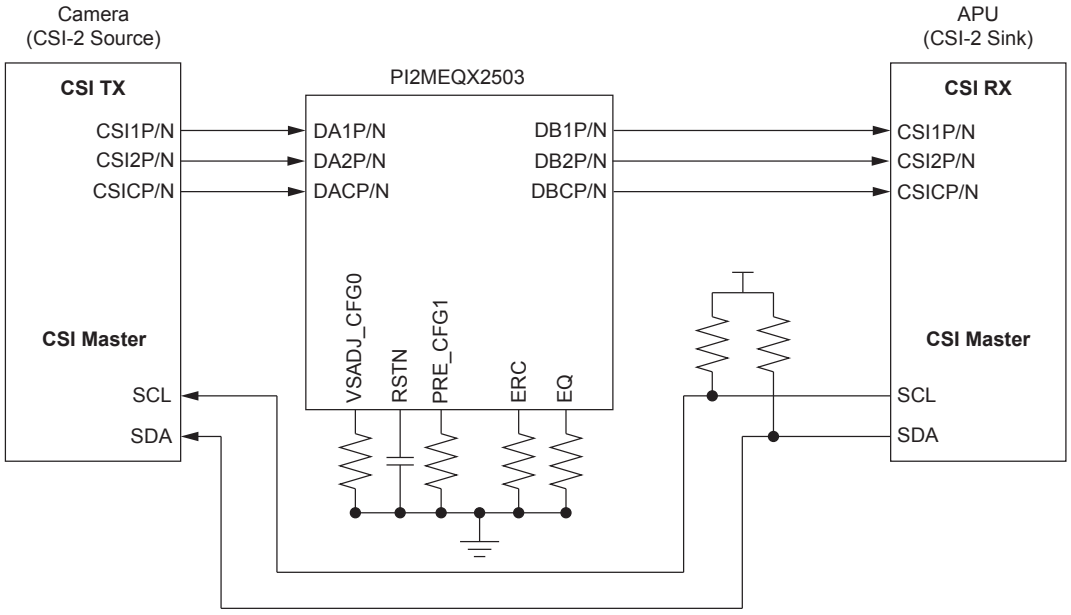
Notes:

- E = Pb-free and Green
- X suffix = Tape/Reel

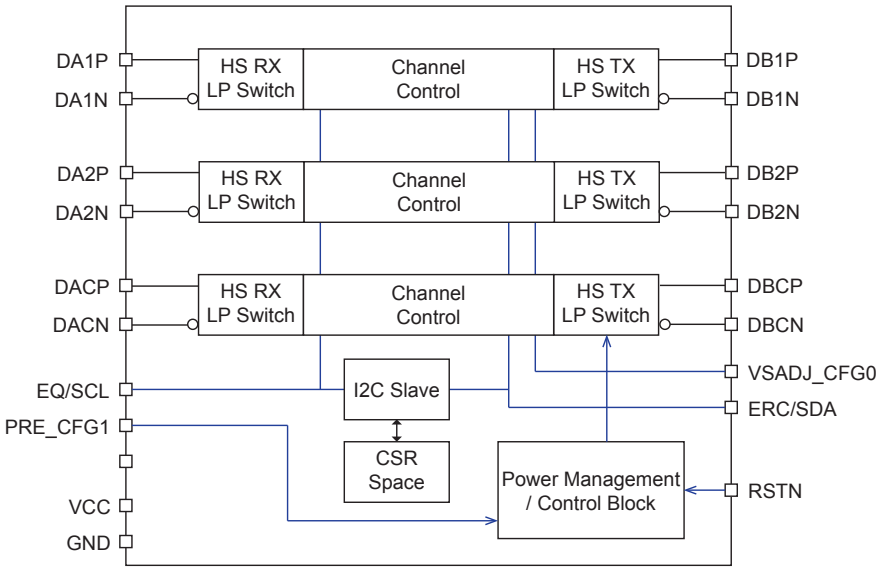
Notes:

1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.
2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.

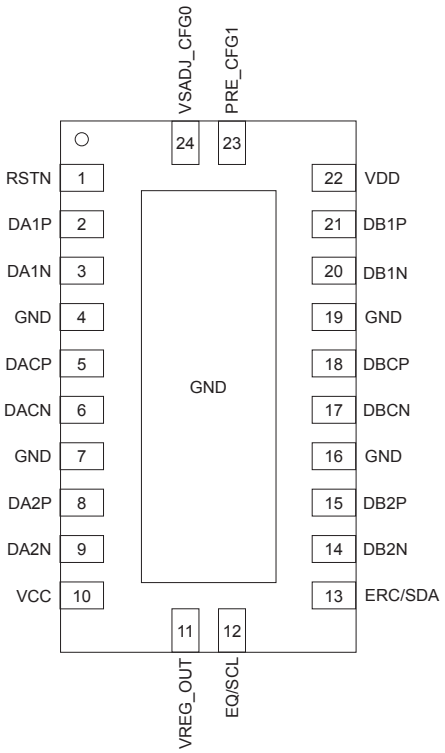
Application Schematic



Functional Block Diagram



Pin Configuration



Pin Description

Pin Number	Pin Name	Type	Description
1	RSTN	I	Reset, active low. When low, all internal CSR are reset to default and PI2MEQX2503 is placed in low power state. With internal 300kΩ pull-up resistor.
2	DA1P	100Ω Differential Input	CSI-2/DSI Lane 1 Differential positive Input. If unused, this pin should be tied to GND.
3	DA1N		CSI-2/DSI Lane 1 Differential negative input. If unused, this pin should be tied to GND.
5	DACP	100Ω Differential Input	CSI-2/DSI Differential Clock positive Input
6	DACN		CSI-2/DSI Differential Clock negative Input
8	DA2P	100Ω Differential Input	CSI-2/DSI Lane 2 Differential positive Input. If unused, this pin should be tied to GND.
9	DA2N		CSI-2/DSI Lane 2 Differential negative Input. If unused, this pin should be tied to GND.
10	VCC	Power	1.8V (±10%) Supply.
11	VREG_OUT	Power	1.2V Regulator Output. Requires a 0.1μF capacitor to GND.

Pin Number	Pin Name	Type	Description
12	EQ/SCL	I/O (3-level)	RX Equalization Select. Pin state sampled on rising edge of RSTN. This pin also functions as I2C SCL pin. EQ/SCL = V_{IL}: Equalization = 3dB EQ/SCL = V_{IM}: Equalization = 6dB EQ/SCL = V_{IH}: Equalization = 9dB With internal 100kΩ pull -up and pull-down resistor, default V_{IM}
13	ERC/SDA	I/O (3-level)	Edge Rate Control for DB[4:0]P/N High speed transmitter rise and fall time. Pin state sampled on rising edge of RSTN. This pin also functions as I2C SDA pin. ERC/SDA = V_{IL}: Edge rate = 200ps ERC/SDA = V_{IM}: Edge rate = 150ps ERC/SDA = V_{IH}: Edge rate = 250ps With internal 100kΩ pull -up and pull-down resistor, default V_{IM}
14	DB2N	100Ω Differential Output	CSI-2/DSI Lane 2 Differential negative Output. If unused, this pin should be left unconnected.
15	DB2P		CSI-2/DSI Lane 2 Differential positive Output. If unused, this pin should be left unconnected.
17	DBCN	100Ω Differential Output	CSI-2/DSI Differential Clock negative Output
18	DBCP		CSI-2/DSI Differential Clock positive Output
20	DB1N	100Ω Differential Output	CSI-2/DSI Lane 1 Differential negative Output. If unused, this pin should be left unconnected.
21	DB1P		CSI-2/DSI Lane 1 Differential positive Output. If unused, this pin should be left unconnected.
22	VDD	Power	This pin must be connected to the VREG_OUT pin through at least a 10-mil trace and a 0.1µF capacitor to ground.
23	PRE_CFG1	I/O (3-level)	Controls DPHY TX HS pre-emphasis level and the LP TX rise and fall times. Pin state is sampled on the rising edge of RSTN. PRE_CFG1 = V_{IL}: Pre-emphasis level = 0dB PRE_CFG1 = V_{IM}: Pre-emphasis level = 1dB PRE_CFG1 = V_{IH}: Pre-emphasis level = 3dB With internal 100kΩ pull -up and pull-down resistor, default V_{IM}
24	VSADJ_ CFG0	I (3-level)	Controls output voltage swing for DB HS transmitters and the LP TX rise and fall times. Pin state is sampled on the rising edge of RSTN. VSADJ_CFG0 = V_{IL}: Swing = 225mV VSADJ_CFG0 = V_{IM}: Swing = 250mV VSADJ_CFG0 = V_{IH}: Swing = 275mV With internal 100kΩ pull -up and pull-down resistor, default V_{IM}
4, 7, 16, 19, Center Pad	GND	GND	Ground connection. The thermal pad must be connected to GND in order to optimize the thermal characteristics of the package.

Feature Description

HS Receive Equalization

The PI2MEQX2503 supports three levels of receive equalization to compensate for ISI loss in the channel. These three levels are 3dB, 6dB, and 9dB at 1.25GHz. The equalization level used by the PI2MEQX2503 is determined by the state of the EQ/SCL pin at the rising edge of RSTN. If necessary, the receiver equalization level can also be set through writing to the RXEQ register via the local I2C interface.

Table 1. EQ/SCL Pin Function

EQ/SCL Pin	HS Rx Equalization
≤ V_{IL}	3dB
V_{IM}	6dB at 1.25GHz
≥ V_{IH}	9dB at 1.25GHz

HS TX Edge Rate Control

Table 2. HS TX Edge Rate Control

EQ/SDA Pin	HS Rise/Fall Times
≤ V_{IL}	200ps typical
V_{IM}	150ps typical
≥ V_{IH}	250ps typical

I2C Slave Address

Bit 7	Bit 6	Bit 5	Bit 4	Bit 3	Bit 2	Bit 1	Bit 0 (W/R)
1	1	0	1	1	0	0	0/1

Register Map

Address	Register	Type	Bit 7	Bit 6	Bit 5	Bit 4	Bit 3	Bit 2	Bit 1	Bit 0
00h	Device ID	Read	Device ID (PI2MEQX2503): (reset value: 00000101b)							
01h	Version ID	Read	Version ID (Version 0): (reset value: 00000000b)							
02h	EQ	Read/Write	Reserved (reset value: 0000b)				EQ <3>	EQ <2>	EQ <1>	EQ <0>
03h	ERC	Read/Write	Reserved (reset value: 00000b)					ERC <2>	ERC <1>	ERC <0>
04h	Reserved	Read	Reserved (reset value: 00001000b)							
05h	Output Pre-emphasis & Swing	Read/Write	Reserved (reset value: 0110b)				PREEMP LEVEL <1>	PREEMP LEVEL <0>	VSADJ <1>	VSADJ <0>

Register Setting for EQ/ERC/PRE_CFG1/VSADJ_CFG0

EQ<3:0> (Register 02h<3:0>)	EQ Gain at 500MHz	EQ Gain at 1.25GHz
0000	0dB	0dB
0010	2dB	3dB
0110	4dB	6dB
1011	6dB	9dB
Others	Reserved	Reserved

ERC<2:0> (Register 03h<2:0>)	Edge Rate Control
001	250ps
011	200ps
111	150ps
Others	Reserved

PREEMP LEVEL<1:0> (Register 05h<3:2>)	Pre-emphasis Level
00	0dB
01	1dB
11	3dB
Others	Reserved

VSADJ<1:0> Register 05h<1:0>	Output Voltage Swing
00	200mV
01	225mV
10	250mV
11	275mV

Bus Transaction

Writing to the Registers

Data is transmitted to the PI2MEQX2503 by sending the device address and setting the least significant bit to a logic 0. The register sub-address byte is sent after the address and determines which register will receive the data following the sub-address byte.

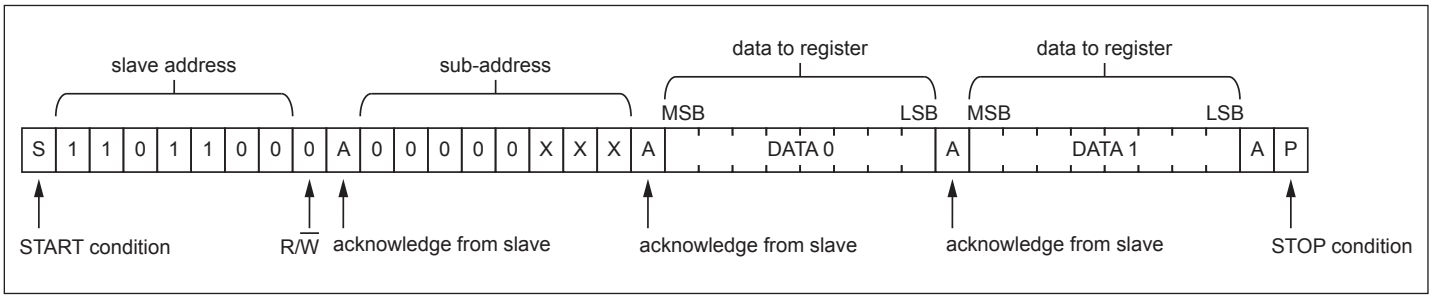


Figure 1. Write to Register

Reading the Register

In order to read data from the PI2MEQX2503, the bus master must first send the PI2MEQX2503 address with the least significant bit set to a logic 0. The sub-address byte is sent after the address and determines which register will be accessed. After a restart, the device address is sent again, but this time the lease significant bit is set to a logic 1. Data from the register defined by the sub-address byte will then be sent by the PI2MEQX2503. Data is clocked into the register on the falling edge of the acknowledge clock pulse.

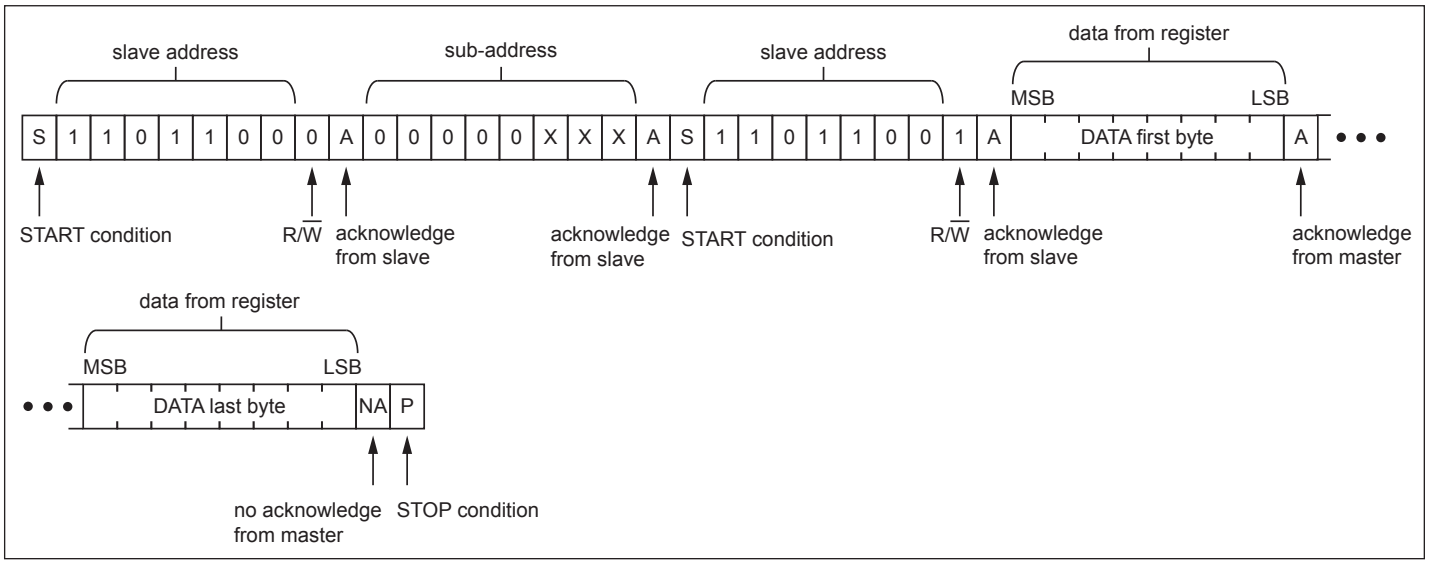


Figure 2. Read from Register

Maximum Ratings

(Above which useful life may be impaired. For user guidelines, not tested.)

Storage Temperature . . . . . –65°C to +150°C
Supply Voltage to Ground Potential . . . . . –0.3V to +2.175V
Voltage Range
D-PHY Lane I/O Differential Voltage . . . . . –0.3V to +1.4V
RSTN . . . . . –0.3V to +2.175V
All Other Terminals . . . . . –0.3V to +2.175V
Max Junction Temperature . . . . . 105°C

Note:
Stresses greater than those listed under MAXIMUM RATINGS may cause permanent damage to the device. This is a stress rating only and functional operation of the device at these or any other conditions above those indicated in the operational sections of this specification is not implied. Exposure to absolute maximum rating conditions for extended periods may affect reliability.

ESD Rating

Symbol	Parameter	Conditions	Value	Units
$V_{(ESD)}$	Electrostatic discharge	Human-body model (HBM), per ANSI/ESDA/JEDEC JS-001[1]	2000	V
		Charged-device model (CDM), per JEDEC specification JESD22-C101[2]	1000	V

Recommended Operating Conditions

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Units
V_{CC}	Supply voltage		1.62	1.8	1.98	V
T_A	Operating free-air temperature		-40		85	°C

Electrical Characteristics, Power Supply

Over operating free-air temperature range (unless otherwise noted)

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Units
PACTIVE	Power under normal operation for 2 data lanes + clock.	D-PHY Lanes at 2.5Gbps; V_{CC} supply stable, V_{CC} = 1.8V		80	120	mW
P_LP11	LP11 Power	All D-PHY lanes in LP11; V_{CC} supply stable; V_{CC} = 1.8V		2	5	mW
P_STB	Standby mode power	RSTN held in asserted state (low); V_{CC} supply stable; V_{CC} = 1.8V		0.02	0.2	mW
P_ULPS	ULPS mode power	IC stay in ULPS mode; V_{CC} supply stable; V_{CC} = 1.8V		2	5	mW

Electrical Characteristics

Over operating free-air temperature range (unless otherwise noted)

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Units
Standard IO (RSTN, ERC, EQ, CFG[1:0])						
V_{IL}	Low-level control signal input voltage		0		$0.14xV_{CC}$	V
V_{IM}	Mid-level control signal input voltage		$0.45xV_{CC}$	$V_{CC}/2$	$0.55xV_{CC}$	V
V_{IH}	High-level control signal input voltage		$0.86xV_{CC}$		VCC	V
V_F	Floating Voltage	V_{IN} = High Impedance		$V_{CC}/2$		V
V_{OL}	Low level output voltage (open-drain). ERC (SDA) only	At I_{OL} max.			$0.2xV_{CC}$	V
I_{OL}	Low Level Output Current				3	mA
I_{IH}	High level input current				±36	µA
I_{IL}	Low level input current				±36	µA
R_{PU}	Internal pull-up resistance			100		kΩ
R_{PD}	Internal pull-down resistance			100		kΩ
$R_{(RSTN)}$	RSTN control input pullup resistor			300		kΩ
SCL, SDA						
V_{IL}	Low-level I2C signal input voltage				$0.3xV_{CC}$	V
V_{IH}	High-level I2C signal input voltage		$0.7xV_{CC}$			V
MIPI Input Leakage (DA1P/N, DACP/N)						
I_{lkg}	Input leakage current	V_{CC} = 0V; V_{DD} = 0V; MIPI D-PHY pulled up to 1.35V	-65		65	µA
MIPI D-PHY HS Receiver Interface (DA1P/N, DA2P/N, DACP/N)						
$V_{(CM-RX\_DC)}$	Differential Input Common-mode voltage HS Receive mode	$V_{(CM-RX)} = (V_{A\,x\,P} + V_{A\,x\,N})/2$	70		330	mV
$\lvert V_{ID} \rvert$	HS Receiver input differential voltage	$\lvert V_{ID} \rvert = \lvert V_{A\,x\,P} - V_{A\,x\,N} \rvert$ <1.5Gbps	70			mV
		$\lvert V_{ID} \rvert = \lvert V_{A\,x\,P} - V_{A\,x\,N} \rvert$ >1.5Gbps	40			mV
$V_{IH(HS)}$	Single-ended input high voltage				460	mV
$V_{IL(HS)}$	Single-ended input low voltage		-40			mV
$R_{(DIFF-HS)}$	Differential input impedance		75	100	125	Ω
$V_{(RXEQ0)}$	Rx EQ gain when EQ/SCL pin ≤ V_{IL}			3		dB

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Units
$V_{(RXEQ1)}$	Rx EQ gain when EQ/SCL pin = V_{IM}	At 1250MHz		6		dB
$V_{(RXEQ2)}$	Rx EQ gain when EQ/SCL pin ≥ V_{IH}	At 1250MHz		9		dB
MIPI D-PHY LP Receiver Interface (DA1P/N, DA2P/N, DACP/N)						
$V_{(LPIH)}$	LP Logic 1 Input Voltage		880			mV
$V_{(LPIL)}$	LP Logic 0 Input voltage				550	mV
$V_{(HYST)}$	LP Input Hysteresis		25			mV
MIPI D-PHY HS Transmitter Interface (DB1P/N, DB2P/N, DBCP/N)						
$V_{(CMTX)}$	HS Transmit static common-mode voltage, VSADJ_CFG0 = VIL	$V_{(CMTX)} = (V_{(BP)} + V_{(BN)})/2$	150	200	250	mV
$\lvert\Delta V_{(CMTX)(1,0)}\rvert$	VCMTX mismatch when output is differential-1 or differential-0	$\Delta V_{(CMTX)(1,0)} = (V_{(CMTX)(1)} - V_{(CMTX)(0)})/2$			5	mV
$\lvert V_{OD(VD0)}\rvert$	HS Transmit differential voltage, VSADJ_CFG0 = VIL	$\lvert V_{OD}\rvert = \lvert V_{(DP)} - V_{(DN)}\rvert$	140	200	270	mV
$\lvert\Delta V_{OD}\rvert$	V_{OD} mismatch when output is differential-1 or differential-0	$\Delta V_{OD} = \lvert\Delta V_{O(D1)}\rvert - \lvert\Delta V_{O(D0)}\rvert$			14	mV
$V_{OH(HS)}$	HS Output high voltage for non-transition bit	CFG0 ≥ V_{IH} HS Pre = 3dB			430	mV
$V_{(PRE1)}$	Pre-emphasis Level for HSTX_PRE_CFG1 = V_{IM}	PRE = 20 x LOG ($V_{OD(TBx)}$ / $V_{OD(VDX)}$), See Figure 1.		1		dB
$V_{(PRE2)}$	Pre-emphasis level for HSTX_PRE_CFG1 = V_{IH}	PRE = 20 x LOG ($V_{OD(TBx)}$ / $V_{OD(VDX)}$), See Figure 1.		3		dB
$R_{pd(HS)}$	Pull down resistor when RSTN = 0V			300		kΩ
LP Mode Switch Interface						
R_{ON_LP}	I_{ON} = -8mA, DA1P/N, DA2P/N, DCP/N = 1.2V	V_{CC} = 1.8V		30	60	Ω
ΔR_{ON_LP}	I_{ON} = -8mA, DA1P/N, DA2P/N, DCP/N = 1.2V	V_{CC} = 1.8V		0.1	0.5	Ω
C_{ON}		V_{CC} = 1.8V		7		pF
-3db BW		V_{CC} = 1.8V; DC bias = 0V		800		MHz

Timing Requirements

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Units
I2C (ERC (SDA), EQ (SCL))						
$t_{HD;STA}$	Hold Time (repeated) START condition. After this period, the first clock pulse is generated		4			µs
t_{LOW}	Low period of SCL clock		4.7			µs
t_{HIGH}	High period of SCL clock		4			µs
$t_{SU;STA}$	Setup time for a repeated START condition		4.7			µs
$t_{HD;DAT}$	Data hold time		5			µs
$t_{SU;DAT}$	Data setup time		4			µs
$t_{SU;STO}$	Setup time for STOP condition		4			µs
t_{BUF}	Bus free time between a STOP and START condition		4.7			µs
RSTN						
t_{D1}	V_{CC} stable before de-assertion of RSTN		100			µs
t_{SU2}	Setup of VSADJ_CFG0, PRE_CFG1, EQ and ERC pin before de-assertion of RSTN		0			µs
t_{h2}	Hold of VSADJ_CFG0, PRE_CFG1, EQ and ERC pin after de-assertion of RSTN		250			µs
t_{VCC_RAMP}	V_{CC} supply ramp requirements		0.2		100	ms
Delay Time for HS Mode						
t_{HSPD}	Propagation delay from DA to DB. In HS mode			1		ns

Switching Characteristics

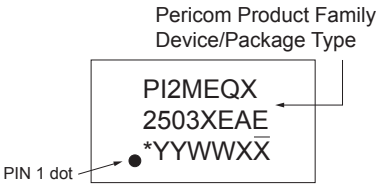
Over operating free-air temperature range (unless otherwise noted)

Symbol	Parameter	Conditions	Min.	Typ.(1)	Max.	Units
I2C (ERC (SDA), EQ (SCL))						
$F_{(SCL)}$	I2C Clock Frequency				100	kHz
t_{F_I2C}	Fall time of both SDA and SCL signals	Load of 350pF with 2-K pul-lup resistor. Measure at 30% - 70%			300	ns
t_{R_I2C}	Rise Time of both SDA and SCL signals				1000	ns
D-PHY Link						
$F_{(BR)}$	Bit Rate				2.5	Gbps
$F_{(HSCLK)}$	HS Clock Input range		100		1250	MHz
MIPI D-PHY HS Receiver Interface (DACP/N, DA1P/N, DA2P/N)						
$\Delta V_{(CMRX\_HF)}$	Common-mode Interface beyond 450MHz				100	mV
		>1.5GHz			50	mV
$\Delta V_{(CMRX\_LF)}$	Common-mode interference 50MHz – 450MHz		-50		50	mV
MIPI D-PHY HS Transmitter Interface (DBCP/N, DB1P/N, DB2P/N)						
$\Delta V_{(CMTX\_HF)}$	Common-level variations above 450MHz				15	mVrms
$\Delta V_{(CMTX\_LF)}$	Common-level variation be-tween 50MHz – 450MHz				25	mVpeak
t_R and t_F	20% - 80% rise time and fall time	Datarate ≤ 1Gbps			0.3	UI
		Datarate > 1Gbps and ≤ 1.5Gbps			0.35	UI
		Datarate > 1.5Gbps			0.4	UI
		Datarate ≤ 1.5Gbps	100			ps
		Datarate > 1.5Gbps	50			ps
D-PHY LP Receiver Interface (DACP/N, DA1P/N, DA2P/N)						
e_{SPIKE}	Input Pulse rejection				300	V ps
$t_{MIN(RX)}$	Minimum pulse width re-sponse		20			ns
$V_{(INT)}$	Peak interference amplitude				200	mV
$F_{(INT)}$	Interference Frequency		450			MHz
MIPI D-PHY LP Transmitter Interface (DBCP/N, DB1P/N, DB2P/N)						
t_{REOT}	30% - 85% rise time and fall time	Measured at end of HS trans-mission.			35	ns

Note:

1. All typical values are at V_{CC} = 1.8V, and T_A = 25°C.

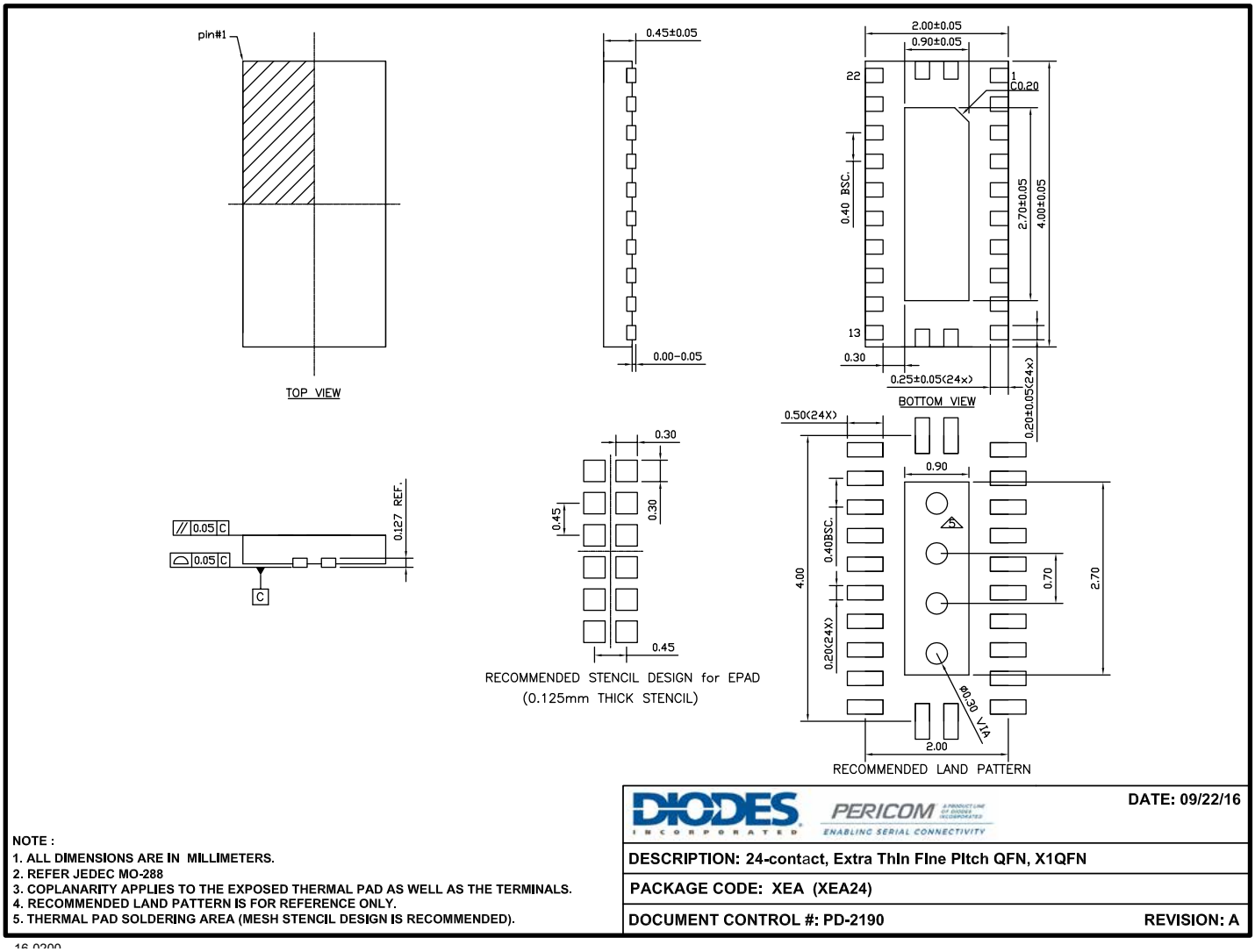
Part Marking



*: Die Rev
YY: Date Code (Year)
WW: Date Code (Workweek)
1st X: Assembly Code
2nd X: Fab Code
Note: Date Code per MA-1251

Package Mechanical

24-X1QFN (XEA)



For latest package information:

See http://www.diodes.com/design/support/packaging/pericom-packaging/packaging-mechanicals-and-thermal-characteristics/.

Tape & Reel Materials and Design

Carrier Tape

The Pocketed Carrier Tape is made of Conductive Polystyrene plus Carbon material (or equivalent). The surface resistivity is 10^6 Ohm/sq. maximum. Pocket tapes are designed so that the component remains in position for automatic handling after cover tape is removed. Each pocket has a hole in the center for automated sensing if the pocket is occupied or not, thus facilitating device removal. Sprocket holes along the edge of the center tape enable direct feeding into automated board assembly equipment. See Figures C and D for carrier tape dimensions.

Cover Tape

Cover tape is made of Anti-static Transparent Polyester film. The surface resistivity is 10^7Ohm/Sq. Minimum to 10^{11}Ohm sq. maximum. The cover tape is heat-sealed to the edges of the carrier tape to encase the devices in the pockets. The force to peel back the cover tape from the carrier tape shall be a MEAN value of 20 to 80gm (2N to 0.8N).

Reel

The device loading orientation is in compliance with EIA-481, current version (Figure B). The loaded carrier tape is wound onto either a 13-inch reel, (Figure D) or 7-inch reel. The reel is made of Anti-static High-Impact Polystyrene. The surface resistivity 10^7Ohm/sq. minimum to 10^{11}Ohm/sq. max.

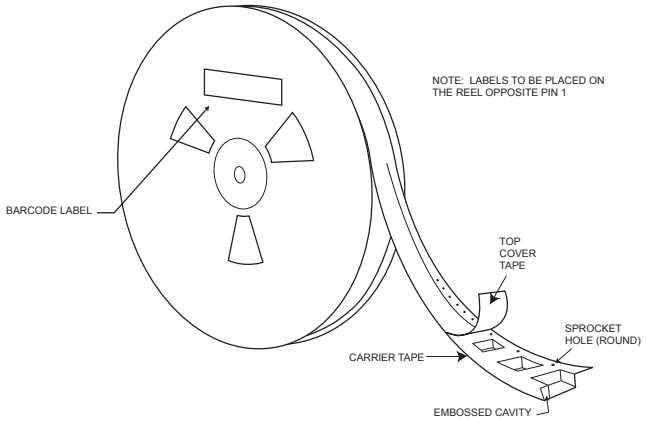


Figure A. Tape & Reel label Information

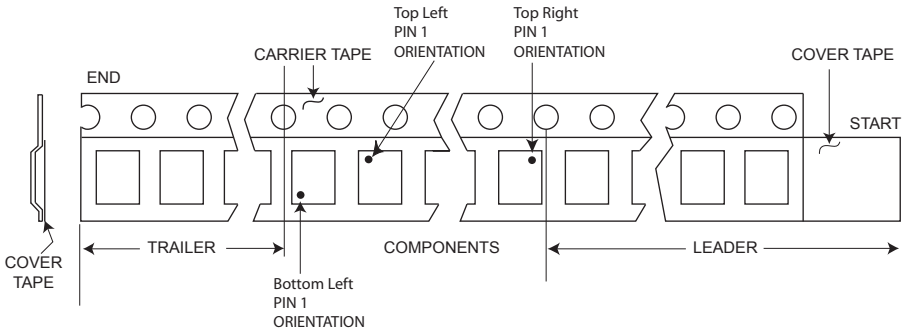


Figure B. Tape Leader and Trailer Pin 1 Orientations

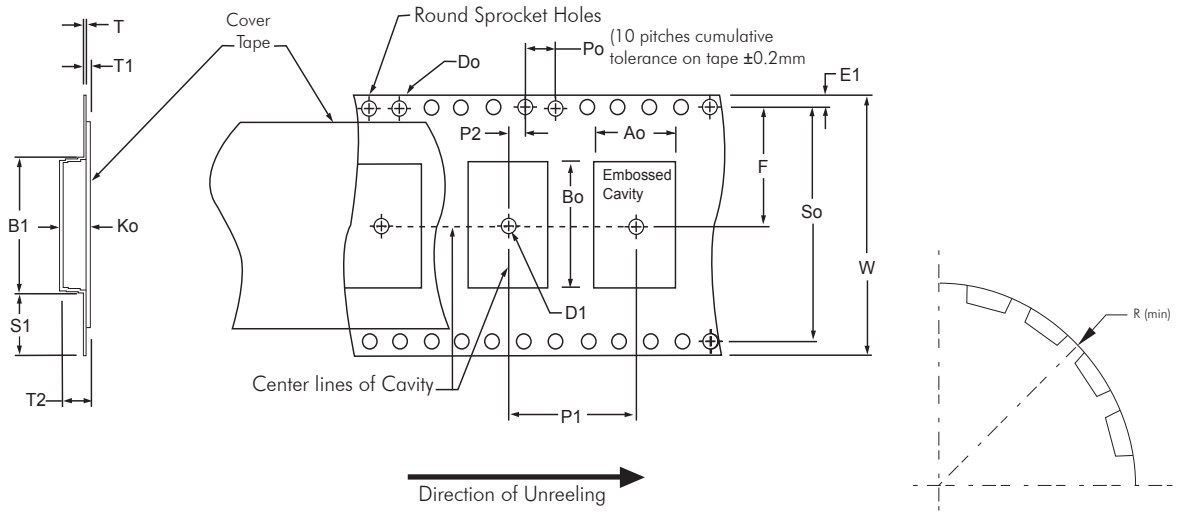


Figure C. Standard Embossed Carrier Tape Dimensions

Constant Dimensions

Tape Size	D_0	D_1 (Min)	E_1	P_0	P_2	R(See Note 2)	S_1 (Min)	T (Max)	T_1 (Max)
8mm	1.5 +0.1 -0.0	1.0	1.75 ± 0.1	4.0 ± 0.1	2.0 ± 0.05	25	0.6	0.6	0.1
12mm		1.5				30			
16mm					2.0 ± 0.1				
24mm									
32mm		2.0				50	N/A (See Note 3)		
44mm					2.0 ± 0.15				

Variable Dimensions

Tape Size	P_1	B_1 (Max)	E_2 (Min)	F	So	T_2 (Max.)	W (Max)	A_0, B_0, & K_0
8mm	Specific per package type. Refer to FR-0221 (Tape and Reel Packing Information)	4.35	6.25	3.5 ± 0.05	N/A (see note 4)	2.5	8.3	See Note 1
12mm		8.2	10.25	5.5 ± 0.05		6.5	12.3	
16mm		12.1	14.25	7.5 ± 0.1		8.0	16.3	
24mm		20.1	22.25	11.5 ± 0.1		12.0	24.3	
32mm		23.0	N/A	14.2 ± 0.1	28.4± 0.1		32.3	
44mm		35.0	N/A	20.2 ± 0.15	40.4 ± 0.1	16.0	44.3	

NOTES:

1. A0, B0, and K0 are determined by component size. The cavity must restrict lateral movement of component to 0.5mm maximum for 8mm and 12mm wide tape and to 1.0mm maximum for 16,24,32, and 44mm wide carrier. The maximum component rotation within the cavity must be limited to 20o maximum for 8 and 12 mm carrier tapes and 10o maximum for 16 through 44mm.
2. Tape and components will pass around reel with radius "R" without damage.
3. S1 does not apply to carrier width ≥32mm because carrier has sprocket holes on both sides of carrier where Do≥S1.
4. So does not exist for carrier ≤32mm because carrier does not have sprocket hole on both side of carrier.

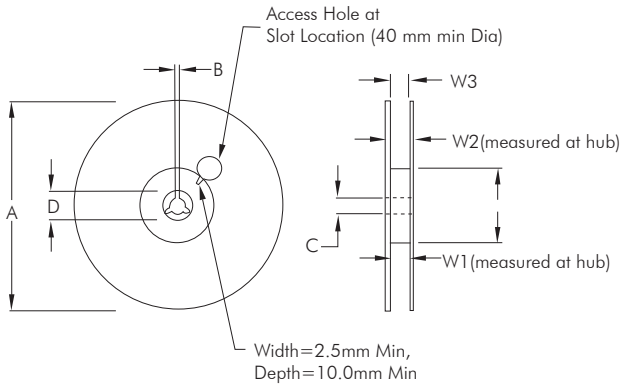


Figure D. Reel Dismensions by Tape Size

Reel Dimensions

Tape Size	A	N (Min) See Note 1	W1	W2(Max)	W3	B (Min)	C	D (Min)
8mm	178 ±2.0mm or 330±2.0mm	60 ±2.0mm or 100±2.0mm	8.4 +1.5/-0.0 mm	14.4 mm	Shall Accommodate Tape Width Without Interference	1.5mm	13.0 +0.5/-0.2 mm	20.2mm
12mm			12.4 +2.0/-0.0 mm	18.4 mm				
16mm	330 ±2.0mm	100 ±2.0mm	16.4 +2.0/-0.0 mm	22.4 mm				
24mm			24.4 +2.0/-0.0 mm	30.4 mm				
32mm			32.4 +2.0/-0.0 mm	38.4 mm				
44mm			44.4 +2.0/-0.0 mm	50.4 mm				

NOTE:

1. If reel diameter A=178 ±2.0mm, then the corresponding hub diameter (N(min) will by 60 ±2.0mm. If reel diameter A=330±2.0mm, then the corresponding hub diameter (N(min)) will by 100±2.0mm.

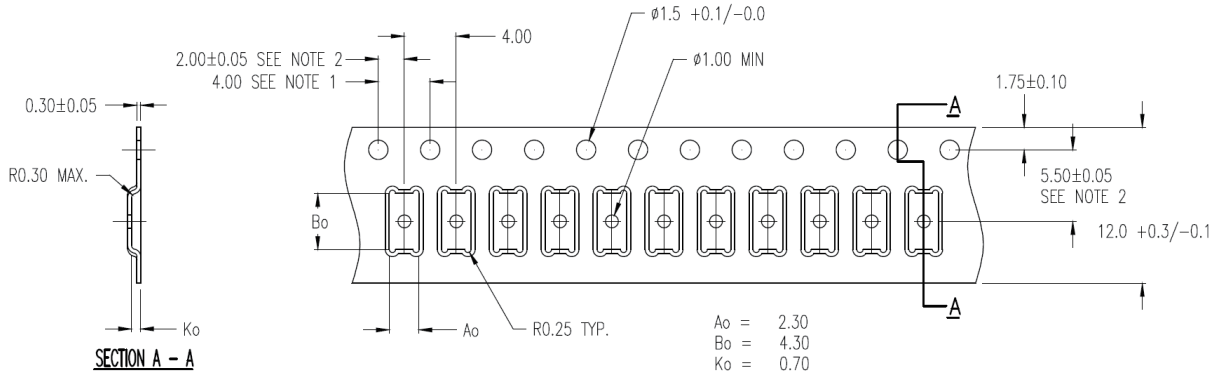


Figure F. PI2MEQX2503 Tape Dimension

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